
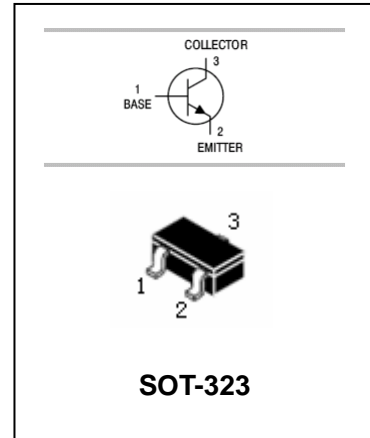


Silicon Epitaxial Planar Transistor

2SC3356W

FEATURES

- Low noise and high gain: $NF=1.1dB$ TYP,
 $G_a=11dB$ TYP. @ $V_{CE}=10V, I_C=7mA, f=1.0GHz$  Lead-free
- High power gain: $MAG=13dB$ TYP.
@ $V_{CE}=10V, I_C=20mA, f=1.0GHz$



APPLICATIONS

- NPN Silicon Epitaxial Planar Transistor.

ORDERING INFORMATION

| Type No. | Marking | Package Code |
|----------|-------------|--------------|
| 2SC3356W | R23/R24/R25 | SOT-323 |

MAXIMUM RATING @ $T_a=25^\circ C$ unless otherwise specified

| Symbol | Parameter | Value | Units |
|----------------|----------------------------------|---------|------------|
| V_{CBO} | Collector-Base Voltage | 20 | V |
| V_{CEO} | Collector-Emitter Voltage | 12 | V |
| V_{EBO} | Emitter-Base Voltage | 3 | V |
| I_C | Collector Current -Continuous | 100 | mA |
| P_C | Collector Dissipation | 200 | mW |
| T_j, T_{stg} | Junction and Storage Temperature | -55~150 | $^\circ C$ |

Silicon Epitaxial Planar Transistor**2SC3356W****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

| Parameter | Symbol | Test conditions | MIN | TYP | MAX | UNIT |
|-------------------------------------|---------------|-------------------------------|-----|-----|-----|---------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C=10\mu A, I_E=0$ | 20 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C=1mA, I_B=0$ | 12 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E=10\mu A, I_C=0$ | 3 | | | V |
| Collector cut-off current | I_{CBO} | $V_{CB}=10V, I_E=0$ | | | 0.1 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB}=1V, I_C=0$ | | | 0.1 | μA |
| DC current gain | h_{FE} | $V_{CE}=10V, I_C=20mA$ | 50 | | 300 | |
| Transition frequency | f_T | $V_{CE}=10V, I_C=20mA$ | | 6 | | GHz |
| Noise figure | F | $V_{CE}=10V, I_C=7mA, f=1GHz$ | | | 2 | dB |

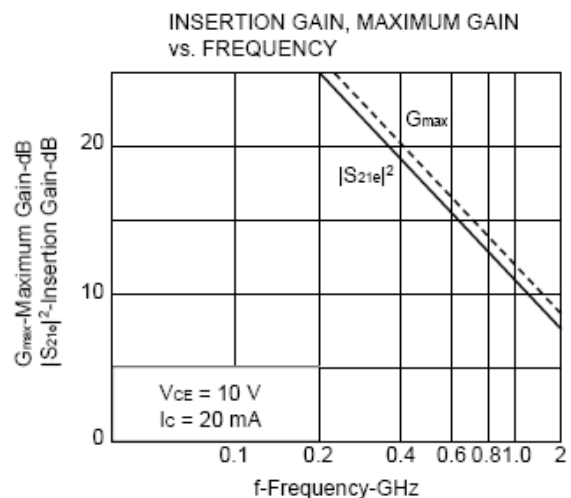
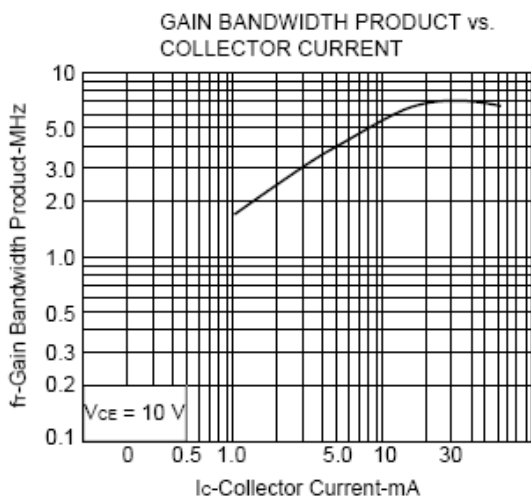
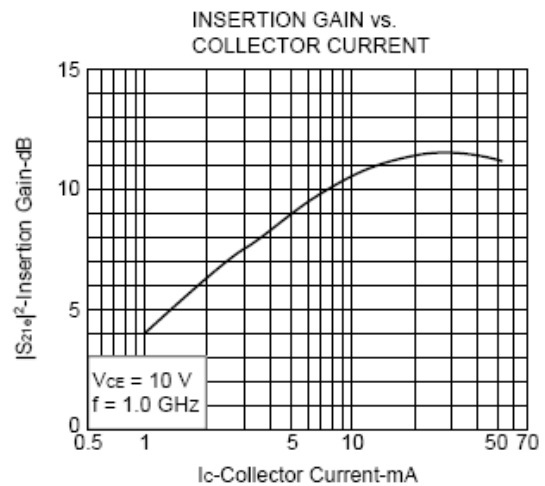
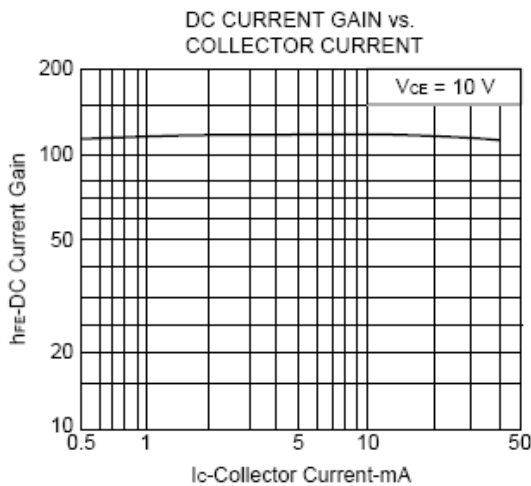
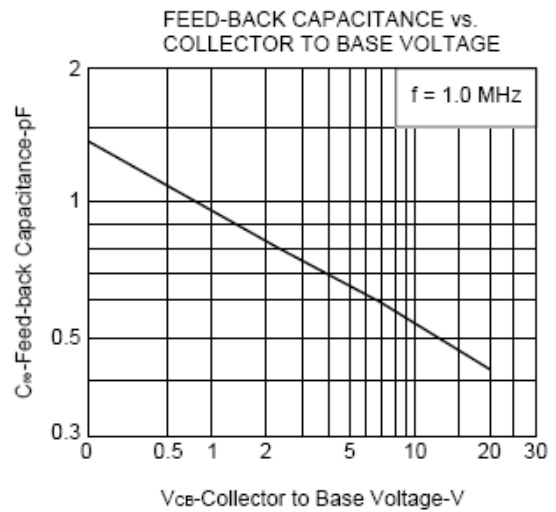
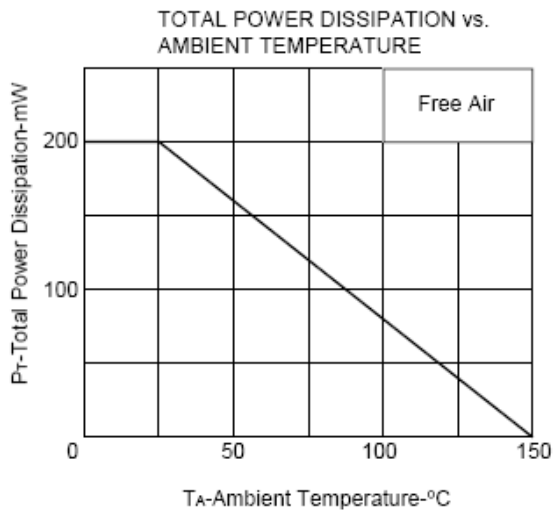
CLASSIFICATION OF $h_{FE(1)}$

| Rank | Q | R | S |
|---------|--------|--------|---------|
| Range | 50-100 | 80-160 | 125-250 |
| Marking | R23 | R24 | R25 |

Silicon Epitaxial Planar Transistor

2SC3356W

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



Silicon Epitaxial Planar Transistor

2SC3356W

PACKAGE OUTLINE

Plastic surface mounted package

SOT-323

| SOT-323 | | |
|----------------------|------------|------|
| Dim | Min | Max |
| A | 1.8 | 2.2 |
| B | 1.15 | 1.35 |
| C | 1.0Typical | |
| D | 0.15 | 0.35 |
| E | 0.25 | 0.40 |
| G | 1.2 | 1.4 |
| H | 0.02 | 0.1 |
| J | 0.1Typical | |
| K | 2.1 | 2.3 |
| All Dimensions in mm | | |

PACKAGE INFORMATION

| Device | Package | Shipping |
|----------|---------|----------------|
| 2SC3356W | SOT-323 | 3000/Tape&Reel |